MMDL770T1G

Schottky Barrier Diode

Schottky barrier diodes are designed primarily for high−efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance − 1.0 pF @ 20 V
- Low Reverse Leakage − 200 nA (max)
- High Reverse Voltage − 70 V (min)
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) @T_A = 25°C Derate above 25°C	P_D	200 1.57	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

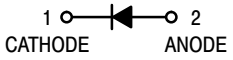
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

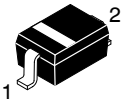
1. FR−5 Minimum Pad

ON Semiconductor®

http://onsemi.com

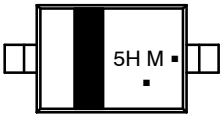
1.0 pF SCHOTTKY BARRIER DIODE





SOD−323
CASE 477
STYLE 1

MARKING DIAGRAM



5H = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMDL770T1G	SOD−323 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 μA)	$V_{(BR)R}$	70	–	–	V
Diode Capacitance (V_R = 20 V, f = 1.0 MHZ)	C_T	–	0.5	1.0	pF
Reverse Leakage (V_R = 35 V)	I_R	–	9.0	200	nAdc
Forward Voltage (I_F = 1.0 mAdc) (I_F = 10 mA)	V_F	– –	0.42 0.7	0.5 1.0	Vdc

TYPICAL CHARACTERISTICS

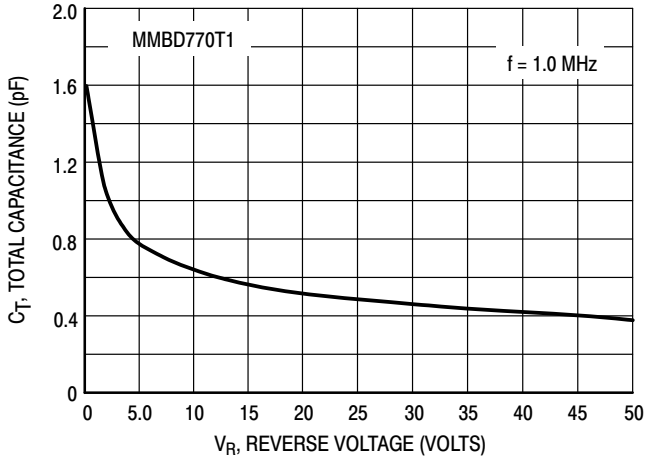


Figure 1. Total Capacitance

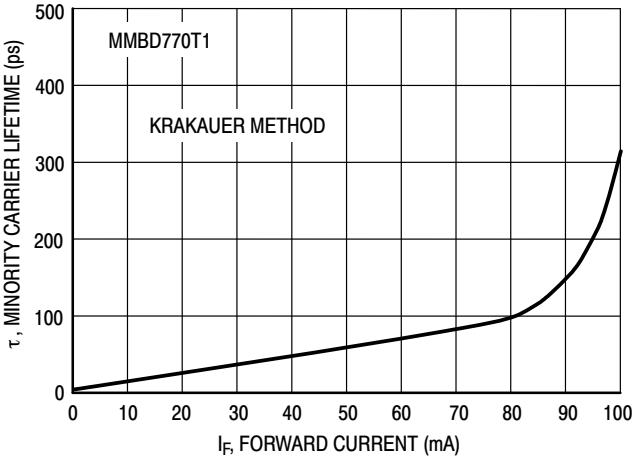


Figure 2. Minority Carrier Lifetime

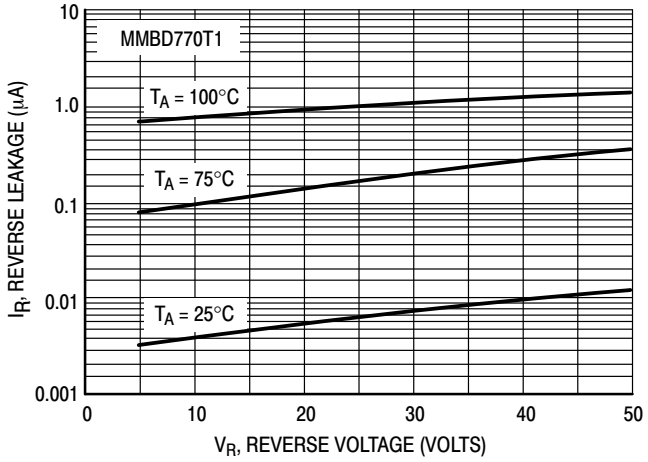


Figure 3. Reverse Leakage

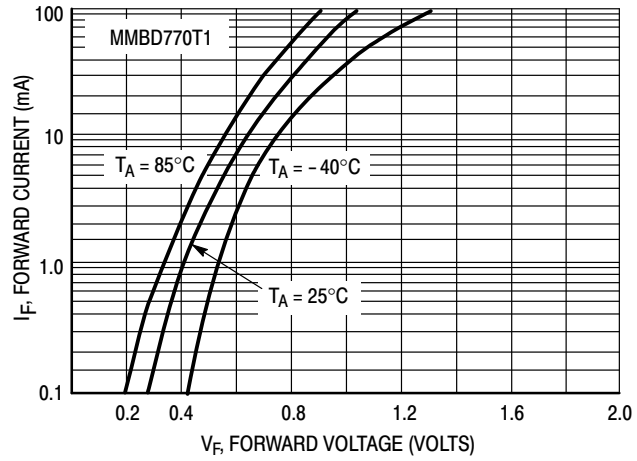
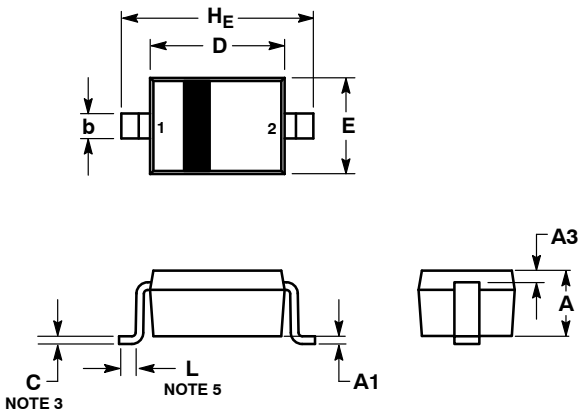


Figure 4. Forward Voltage

MMDL770T1G

PACKAGE DIMENSIONS

SOD−323
CASE 477−02
ISSUE H

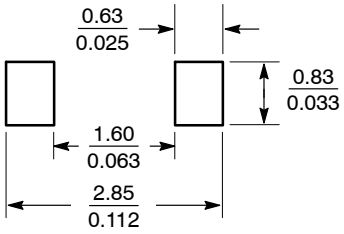


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3		0.15 REF			0.006 REF	
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H_E	2.30	2.50	2.70	0.090	0.098	0.105

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MMDL770T1/D